

## PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1  
Stylesheet Version v1.2

EPAS ID: PAT5777440

<b>SUBMISSION TYPE:</b>	NEW ASSIGNMENT
<b>NATURE OF CONVEYANCE:</b>	ASSIGNMENT
<b>SEQUENCE:</b>	2

**CONVEYING PARTY DATA**

Name	Execution Date
SUNEDISON SEMICONDUCTOR LIMITED (UEN201334164H)	06/06/2018

**RECEIVING PARTY DATA**

<b>Name:</b>	GLOBALWAFERS CO., LTD.
<b>Street Address:</b>	NO. 8 INDUSTRIAL EAST ROAD 2
<b>Internal Address:</b>	SCIENCE-BASED INDUSTRIAL PARK
<b>City:</b>	HSINCHU
<b>State/Country:</b>	TAIWAN

**PROPERTY NUMBERS Total: 1**

Property Type	Number
<b>Application Number:</b>	16235677

**CORRESPONDENCE DATA****Fax Number:** (314)612-2307***Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.*****Phone:** 314-621-5070**Email:** USpatents@armstrongteasdale.com, clager@armstrongteasdale.com**Correspondent Name:** PATENT DOCKET DEPT ARMSTRONG TEASDALE LLP**Address Line 1:** 7700 FORSYTH BOULEVARD**Address Line 2:** SUITE 1800**Address Line 4:** ST. LOUIS, MISSOURI 63105

<b>ATTORNEY DOCKET NUMBER:</b>	28744-4956 (140061.3)
<b>NAME OF SUBMITTER:</b>	MICHAEL G. MUNSELL
<b>SIGNATURE:</b>	/Michael G. Munsell/
<b>DATE SIGNED:</b>	10/18/2019

**Total Attachments: 7**

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## ASSIGNMENT

This Assignment is made by and among SunEdison Semiconductor Limited, a company organized and existing under the laws of Singapore (“SSL”), MEMC Japan Limited, a company organized and existing under the laws of Japan (“MEMC Japan”), and MEMC Electronic Materials, S.P.A., a company organized and existing under the laws of Italy (“MEMC EM”, and collectively with SSL and MEMC Japan, the “Assignors”), and GlobalWafers Co., Ltd., a company organized and existing under the laws of Taiwan and having its registered address at No. 8, Industrial East Road, Science-Based Industrial Park, Hsinchu, Taiwan, R.O.C. (hereinafter referred to as “Assignee”);

**WHEREAS**, on December 31, 2016, Assignors entered into certain IP Transfer Agreements with Assignee;

**WHEREAS**, the parties hereto desire to memorialize, *nunc pro tunc*, the assignment and ownership of all Assigned IP (defined below) for, among other things, recordal purposes with certain patent administration bodies, such as the United States Patent and Trademark Office; and

**WHEREAS**, Assignors acknowledge that payment in full from Assignee for all Assigned IP has heretofore been paid.

**NOW, THEREFORE**, for good and valuable consideration, the receipt and sufficiency of which is hereby acknowledged, Assignors have agreed to and do hereby sell, assign and transfer, and confirm the sale, assignment and transfer, unto Assignee all of their rights, title and interest throughout the world, including without limitation, the right to sue and recover for any past infringements, in and to the Listed IP, any other applications (including provisional, non-provisional, divisional, continuing, or reissue applications) based in whole or in part on any Listed IP, any corresponding patent or patent applications filed in any country based in whole or in part on, and/or claiming priority from, any Listed IP, any patents (including extensions thereof) of any country based in whole or in part on, and/or claiming priority from, any Listed IP, and all of the inventions described in the Listed IP and all of the aforementioned patents and patent applications (all of the foregoing, collectively, the “Assigned IP”);

**TO BE HELD AND ENJOYED** by said Assignee, its successors and assigns, as fully and entirely as the Assigned IP would have been held and enjoyed by Assignors had no assignment of said interest been made.

EACH ASSIGNOR hereby agrees that it will do, execute and deliver, or will cause to be done, executed and delivered, all such further lawful acts, transfers, assignments and conveyances, powers of attorney and assurances for the better assuring, conveying and confirming unto Assignee, all of such Assignor's rights, title and interest in and to the Assigned IP hereby transferred, assigned and conveyed, as Assignee may reasonably require.

*[Signature Pages Follow]*

IN WITNESS WHEREOF, the undersigned have caused these presents to be executed by their respective officers thereunto duly authorized this 6 day of June, 2018.

Assignor:

**SUNEDISON SEMICONDUCTOR LIMITED**

By: *Paul Markowitz*

Name: Paul Markowitz

Title: Director of Intellectual Property

STATE OF Missouri

COUNTY OF St. Charles

On this 6 day of June, 2018, before me, a Notary Public, personally appeared Paul Markowitz, an officer of SUNEDISON SEMICONDUCTOR LIMITED, known to me to be the person who executed the within Assignment, and who did state that said instrument was signed on behalf of said company, and acknowledged to me that he executed the same for the purposes therein stated.

IN TESTIMONY WHEREOF, I have hereunto set my hand and seal the date and year last above written.

*Erika Damiani*  
Notary Public

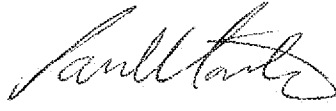
My Commission Expires:

July 20, 2018



Assignor:

**MEMC JAPAN LTD**

By: 


Name: Paul Markowitz

Title: Director of Intellectual Property

STATE OF Missouri  
COUNTY OF St. Charles

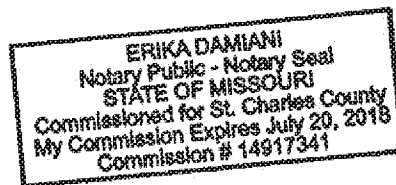
On this 6 day of June, 2018, before me, a Notary Public, personally appeared Paul Markowitz, an officer of MEMC JAPAN LTD, known to me to be the person who executed the within Assignment, and who did state that said instrument was signed on behalf of said company, and acknowledged to me that he executed the same for the purposes therein stated.

IN TESTIMONY WHEREOF, I have hereunto set my hand and seal the date and year last above written.

  
Notary Public

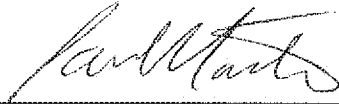
My Commission Expires:

July 20, 2018



Assignor:

**MEMC ELECTRONIC MATERIALS S.P.A.**

By: 


Name: Paul Markowitz

Title: Director of Intellectual Property

STATE OF Missouri  
COUNTY OF St. Charles

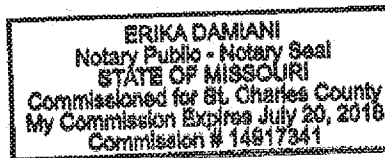
On this 6 day of June, 2018, before me, a Notary Public, personally appeared Paul Markowitz, an officer of MEMC ELECTRONIC MATERIALS S.P.A., known to me to be the person who executed the within Assignment, and who did state that said instrument was signed on behalf of said company, and acknowledged to me that he executed the same for the purposes therein stated.

IN TESTIMONY WHEREOF, I have hereunto set my hand and seal the date and year last above written.

  
Notary Public

My Commission Expires:

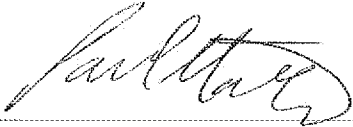
July 20, 2018



For and on behalf of GlobalWafers Co., Ltd.

Assignee:

**GLOBALWAFERS CO., LTD.**

By: 

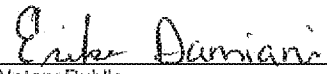
Name: Paul Markowitz

Title: Director of Intellectual Property

STATE OF Missouri )  
COUNTY OF St. Charles

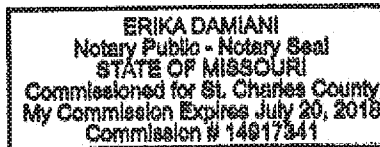
On this 6 day of June, 2018, before me, a Notary Public, personally appeared Paul Markowitz, an officer of GLOBALWAFERS CO., LTD., known to me to be the person who executed the within Assignment, and who did state that said instrument was signed on behalf of said company, and acknowledged to me that he executed the same for the purposes therein stated.

IN TESTIMONY WHEREOF, I have hereunto set my hand and seal the date and year last above written.

  
Notary Public

My Commission Expires:

July 20, 2018





SCHEDULE A

TITLE	Country	Application Number	Filing Date	Publication Number	Publication Date	Patent Number	Issue Date
FEED SYSTEM FOR CRYSTAL GROWING SYSTEMS	US	15/549919	9-Aug-2017	2018-0030614	1-Feb-2018		
HIGH RESISTIVITY SILICON-ON-INSULATOR SUBSTRATE COMPRISING A CHARGE TRAPPING LAYER FORMED BY He-N2 CO-IMPLANTATION	US	15/526864	15-May-2017	2017-0358484	14-Dec-2017		
MANUFACTURING METHOD OF SMOOTHING A SEMICONDUCTOR SURFACE	US	15/775924	14-May-2018				
HIGH RESISTIVITY SILICON-ON-INSULATOR SUBSTRATE COMPRISING A CHARGE TRAPPING LAYER FORMED BY He-N2 CO-IMPLANTATION	US	15/977599	11-May-2018				
SYSTEMS AND METHODS FOR PERFORMING PHASE SHIFT INTERFEROMETRY WHILE A WAFER IS VIBRATING	US	15/534550	9-Jun-2017	2017-0363413	21-Dec-2017		
EPITAXY REACTOR AND SUSCEPTOR SYSTEM FOR IMPROVED EPITAXIAL WAFER FLATNESS	US	15/157745	18-May-2016	2016-0340799	24-Nov-2016		
MANUFACTURE OF GROUP IIIA-NITRIDE LAYERS ON SEMICONDUCTOR ON INSULATOR STRUCTURES	FR	15 63137	22-Dec-2015	3030877	24-Jun-2016		
MANUFACTURE OF GROUP IIIA-NITRIDE LAYERS ON SEMICONDUCTOR ON INSULATOR STRUCTURES	US	15/538474	21-Jun-2017	2018-0005815	4-Jan-2018		
LIQUID DOPING SYSTEMS AND METHODS FOR CONTROLLED DOPING OF A MELT	US	15/556865	8-Sep-2017	2018-0044814	15-Feb-2018		
METHOD OF DEPOSITING CHARGE TRAPPING POLYCRYSTALLINE SILICON FILMS ON SILICON SUBSTRATES WITH CONTROLLABLE FILM STRESS	US	15/554034	28-Aug-2017				
METHOD OF DEPOSITING CHARGE TRAPPING POLYCRYSTALLINE SILICON FILMS ON SILICON SUBSTRATES WITH CONTROLLABLE FILM STRESS	CN	201680025562.9	2-Nov-2017	107533953	2-Jan-2018		

PATENT